

**3N40K-MT**

Preliminary

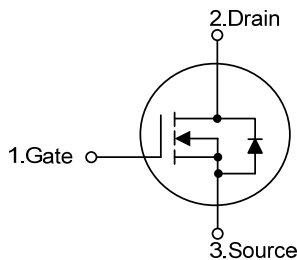
Power MOSFET**3A, 400V N-CHANNEL
POWER MOSFET****DESCRIPTION**

The UTC **3N40K-MT** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology specializes in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **3N40K-MT** is universally applied in electronic lamp ballast based on half bridge topology and high efficient switched mode power supply.

FEATURES

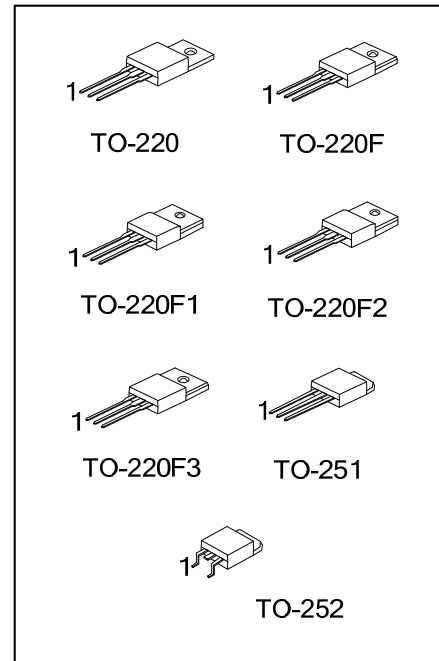
- * $R_{DS(ON)} < 2.0\Omega$ @ $V_{GS} = 10V$, $I_D = 1.5A$
- * High switching speed
- * 100% avalanche tested

SYMBOL**ORDERING INFORMATION**

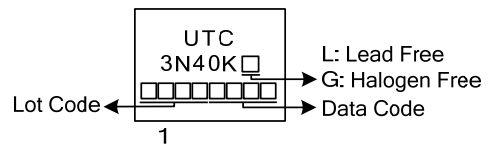
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3N40KL-TA3-T	3N40KG-TA3-T	TO-220	G	D	S	Tube
3N40KL-TF3-T	3N40KG-TF3-T	TO-220F	G	D	S	Tube
3N40KL-TF1-T	3N40KG-TF1-T	TO-220F1	G	D	S	Tube
3N40KL-TF2-T	3N40KG-TF2-T	TO-220F2	G	D	S	Tube
3N40KL-TF3T-T	3N40KG-TF3T-T	TO-220F3	G	D	S	Tube
3N40KL-TM3-T	3N40KG-TM3-T	TO-251	G	D	S	Tube
3N40KL-TN3-R	3N40KG-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

	(1) Packing Type
	(2) Package Type
	(3) Green Package
(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3, TM3: TO-251, TN3: TO-252 (3) L: Lead Free, G: Halogen Free and Lead Free	



■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	400	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous ($T_C=25^{\circ}\text{C}$)	I_D	3	A
	Pulsed (Note 2)	I_{DM}	12	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	290	mJ
	Repetitive (Note 2)	E_{AR}	3	mJ
Power Dissipation	TO-220	P_D	54	W
	TO-220F/TO-220F1		25	W
	TO-220F3		26	W
	TO-220F2		50	W
	TO-251/TO-252		50	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=56\text{mH}$, $I_{AS}=3.0\text{ A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD}\leq 4.4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
	TO-220F1/TO-220F2			
	TO-220F3		110	$^{\circ}\text{C}/\text{W}$
	TO-251/TO-252			
Junction to Case	TO-220	θ_{JC}	2.28	$^{\circ}\text{C}/\text{W}$
	TO-220F/TO-220F1		4.9	$^{\circ}\text{C}/\text{W}$
	TO-220F3			
	TO-220F2		4.8	$^{\circ}\text{C}/\text{W}$
	TO-251/TO-252		2.5	$^{\circ}\text{C}/\text{W}$

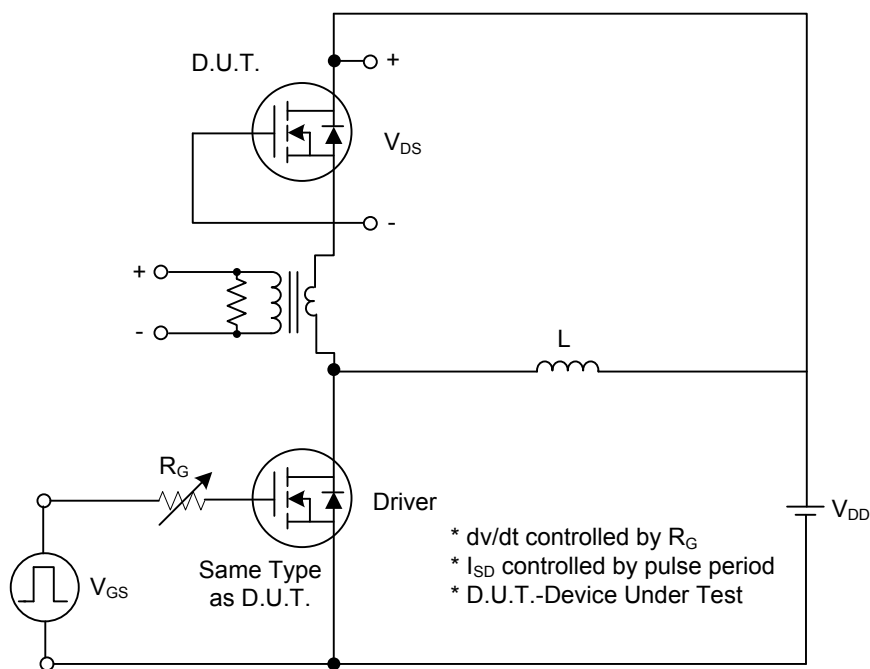
■ **ELECTRICAL CHARACTERISTICS** ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	400			V
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	Reference to 25°C, I _D =250μA		0.38		V/°C
Drain-Source Leakage Current		I _{DSS}	V _{DS} =400V, V _{GS} =0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =1.5A			2.0	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		248	350	pF
Output Capacitance		C _{OSS}			40	80	pF
Reverse Transfer Capacitance		C _{RSS}			5	9	pF
SWITCHING PARAMETERS							
Turn-ON Delay Time		t _{D(ON)}	V _{DS} =30V, I _D =0.5A, R _G =25Ω (Note 1, 2)		40		ns
Rise Time		t _R			48		ns
Turn-OFF Delay Time		t _{D(OFF)}			48		ns
Fall-Time		t _F			27		ns
Total Gate Charge		Q _G	V _{GS} =10V, V _{DS} =50V, I _D =1.3A (Note 1, 2)		12.3	15	nC
Gate to Source Charge		Q _{GS}			4.48		nC
Gate to Drain Charge		Q _{GD}			2.2		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _{SD}				3.0	A
Maximum Body-Diode Pulsed Current		I _{SM}				12	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =3A, V _{GS} =0V			1.5	V

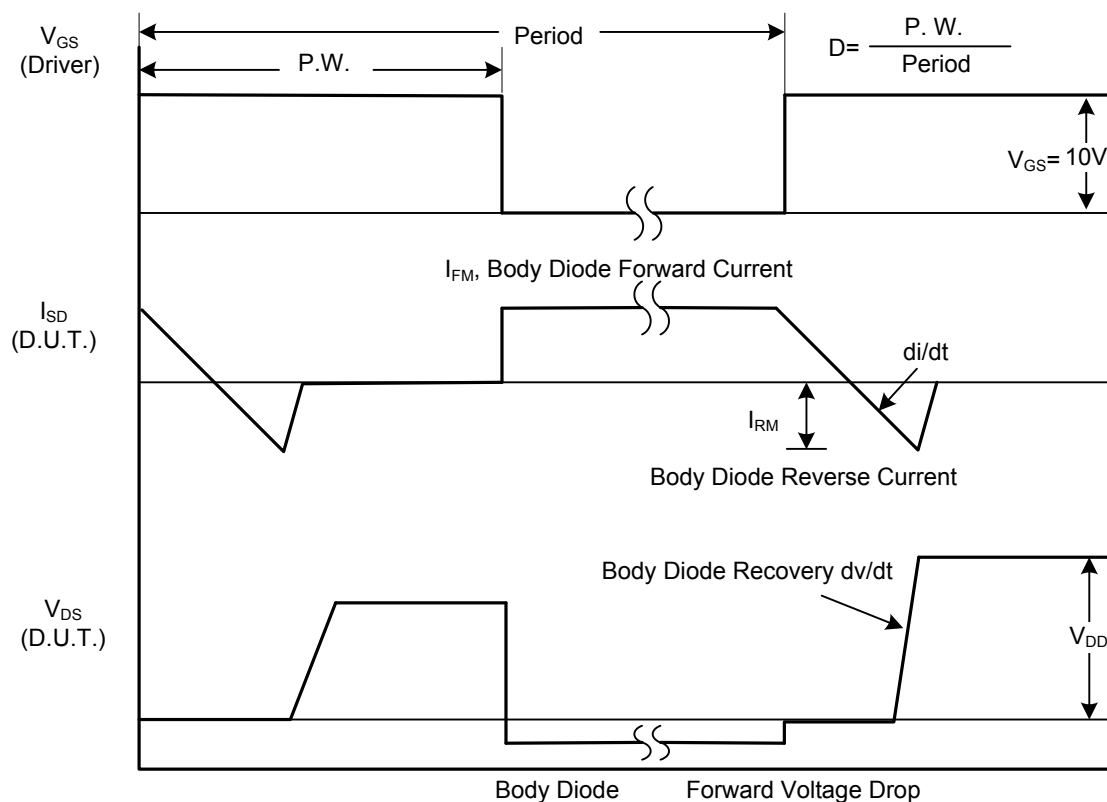
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

TEST CIRCUITS AND WAVEFORMS

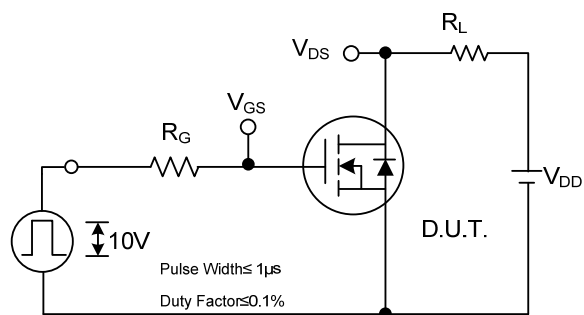


Peak Diode Recovery dv/dt Test Circuit

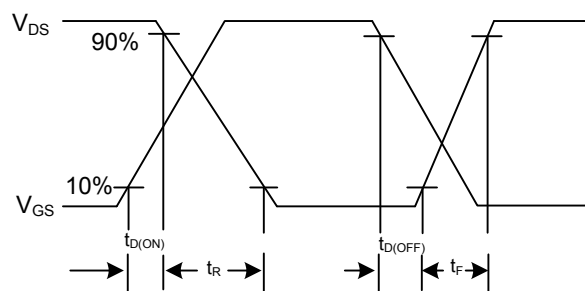


Peak Diode Recovery dv/dt Waveforms

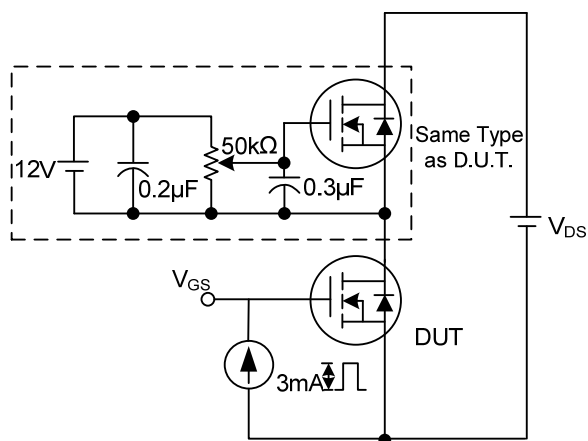
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



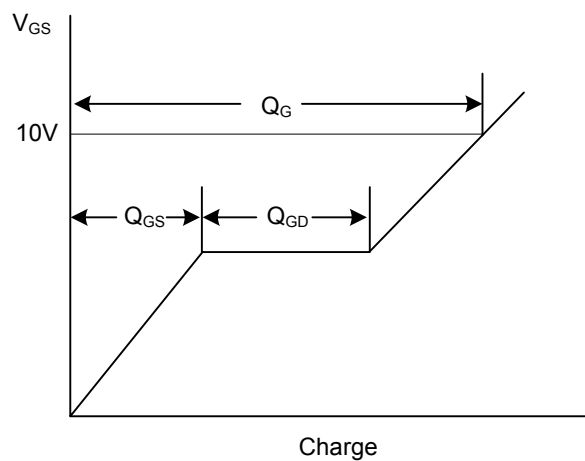
Switching Test Circuit



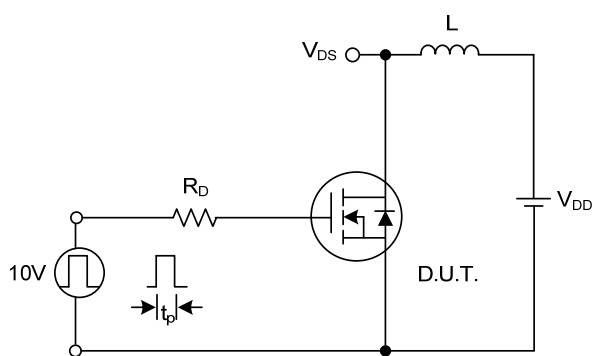
Switching Waveforms



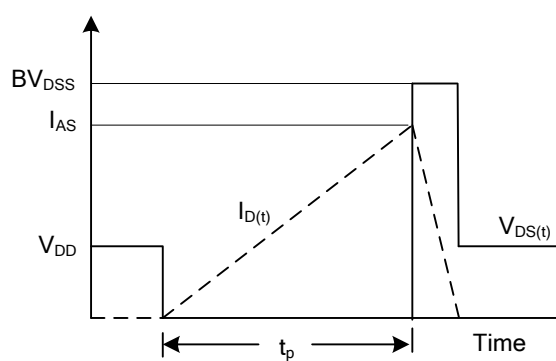
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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